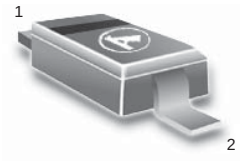
Silicon Epicap Diode

MMVL109T1

26–32 pF VOLTAGE VARIABLE CAPACITANCE DIODES

Designed for general frequency control and tuning applications; providing solid–state reliability in replacement of mechnaical tuning methods.

- High Q with Guaranteed Minimum Values at VHF Frequencies
- Controlled and Uniform Tuning Ratio
- Surface Mount Package
- Device Marking: 4A



PLASTIC, CASE 477
SOD– 323

ORDERING INFORMATION

Device	Package	Shipping
MMVL109T1	SOD–323	3000 / Tape & Reel

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_R	Continuous Reverse Voltage	30	Vdc
I_F	Peak Forward Current	200	mAdc

THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
P_D	Total Device Dissipation FR–5 Board,* T_A = 25°C	200	mW
	Derate above 25°C	1.57	mW/°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	635	°C/W
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +150	°C

*FR–5 Minimum Pad

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 µAdc)	$V_{(BR)R}$	30	—	—	Vdc
Reverse Voltage Leakage Current (V_R = 25 Vdc)	I_R	—	—	0.1	µAdc
Diode Capacitance Temperature Coefficient (V_R = 3.0 Vdc, f = 1.0 MHz)	TC_C	—	300	—	ppm/°C

	C_t, Diode Capacitance V_R = 3.0 Vdc, f = 1.0 MHz pF			Q, Figure of Merit V_R = 3.0 Vdc f = 50 MHz	C_R, Capacitance Ratio C_3/C_{25} f = 1.0 MHz(Note 1)	
Device	Min	Nom	Max	Min	Min	Max
MMVL109T1	26	29	32	200	5.0	6.5

1. C_R is the ratio of C_t measured at 3 Vdc divided by C_t measured at 25 Vdc.

TYPICAL CHARACTERISTICS

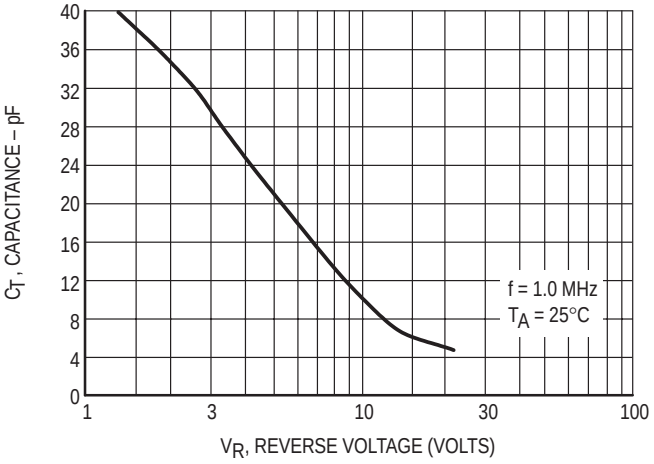


Figure 1. DIODE CAPACITANCE

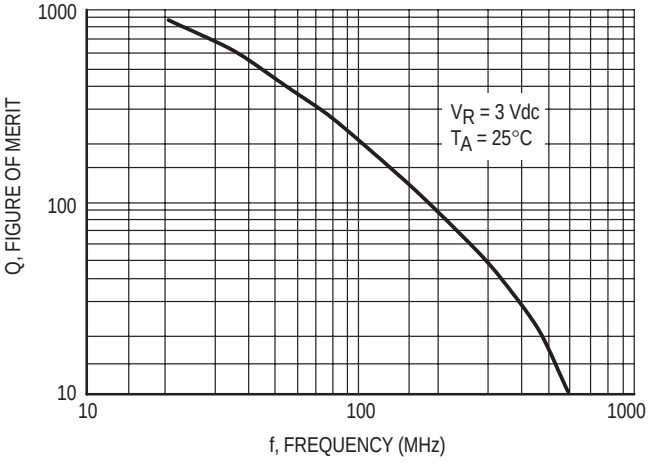


Figure 2. FIGURE OF MERIT

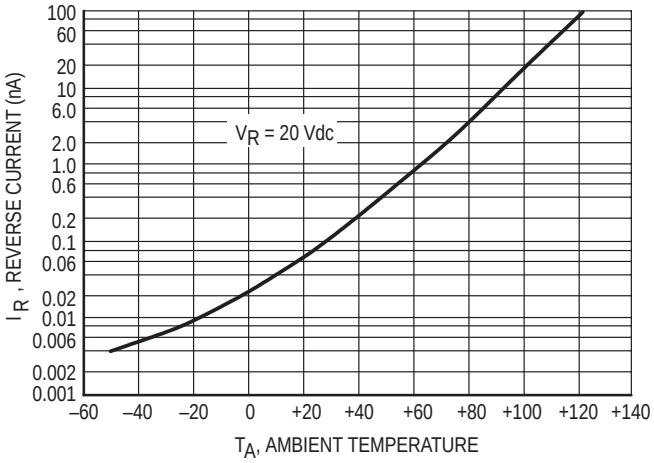


Figure 3. LEAKAGE CURRENT

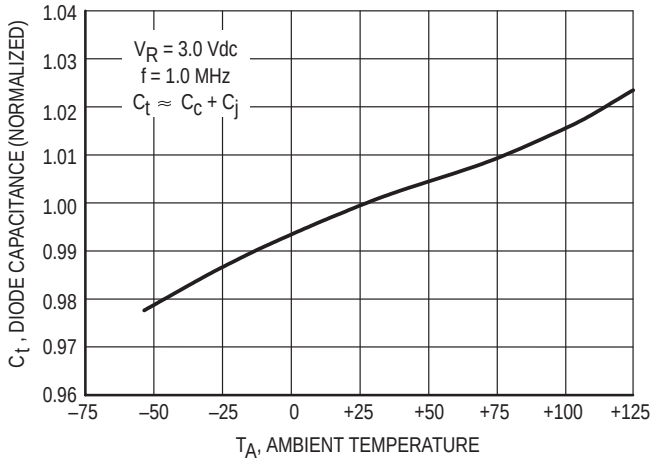


Figure 4. DIODE CAPACITANCE

NOTES ON TESTING AND SPECIFICATIONS

1. C_R is the ratio of C_t measured at 3.0 Vdc divided by C_t measured at 25 Vdc.